

## DATA SHEET

### MMBT2907A

GENERAL PURPOSE TRANSISTOR PNP

**VOLTAGE** -60 Volts **POWER** 300 mW

#### FEATURES

- HIGH DC CURRENT GAIN.
- LOW COLLECTOR-EMITTER SATURATION VOLTAGE BOTH NORMAL AND PB-FREE PACKAGE ARE AVAILABLE.
- LEAD FREE AND HALOGEN-FREE

#### MECHANICAL DATA

- CASE : SOT-23
- TERMINAL : SOLDERABLE PER MIL-STD-202, METHOD 208
- APPROX. WEIGHT:0.008GRAM



CASE : SOT-23

#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

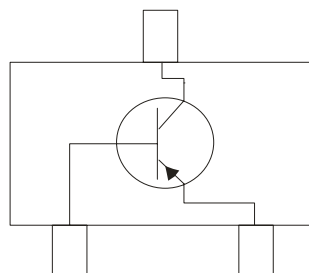
RATINGS AT 25°C AMBIENT TEMPERATURE UNLESS OTHERWISE SPECIFIED.

PARAMETER	SYMBOL	MMBT2907A	UNITS
COLLECTOR-EMITTER VOLTAGE	$V_{CEO}$	-60	V
COLLECTOR-BASE VOLTAGE	$V_{CBO}$	-60	V
EMITTER-BASE VOLTAGE	$V_{EBO}$	-5.0	V
COLLECTOR CURRENT-CONTINUOUS	$I_C$	-600	mA
POWER DISSIPATION @ $T_A = 25^\circ\text{C}$	$P_D$	300	mW
OPERATING AND STORAGE JUNCTION TEMPERATURE RANGE	$T_J; T_{STG}$	-55 TO +150	$^\circ\text{C}$

**NOTE:**

1. Indicates Data in addition to JEDEC Requirements.

**PNP**



## ELECTRICAL CHARACTERISTICS

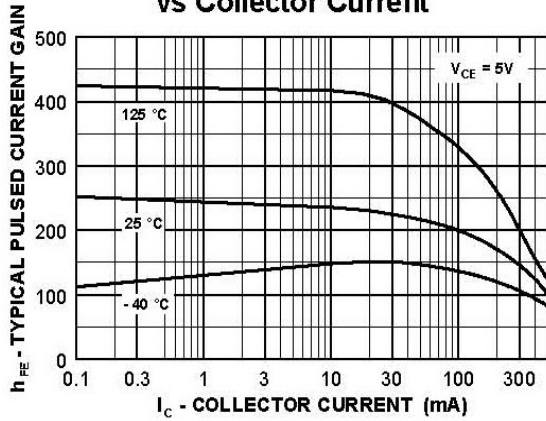
### ELECTRICAL CHARACTERISTICS (AT $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	MIN.	MAX.	UNITS
<b>OFF CHARACTERISTICS</b>					
Collector-Emitter Breakdown Voltage (Note.1)	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-60	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-60	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5.0	-	V
Emitter cut-off Current	$I_{EBO}$	$V_{EB} = -3\text{V}, I_C = 0$	-	-0.1	$\mu\text{A}$
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -50\text{V}, I_E = 0$	-	-0.1	$\mu\text{A}$
Collector Cut-off Current	$I_{CEO}$	$V_{CE} = -3\text{V}, I_B = 0$	-	-0.1	$\mu\text{A}$
<b>ON CHARACTERISTICS</b>					
DC Current Gain	$h_{FE}$	$V_{CE} = -10\text{V}, I_C = -0.1\text{mA}$	75	-	-
		$V_{CE} = -10\text{V}, I_C = -1.0\text{mA}$	100	-	
		$V_{CE} = -10\text{V}, I_C = -10\text{mA}$	100	-	
		$V_{CE} = -10\text{V}, I_C = -150\text{mA}$	100	300	
		$V_{CE} = -10\text{V}, I_C = -500\text{mA}$	50	-	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -150\text{mA}, I_B = -15\text{mA}$	-	-0.4	V
		$I_C = -500\text{mA}, I_B = -50\text{mA}$	-	-1.6	
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = -150\text{mA}, I_B = -15\text{mA}$	-	-1.3	V
		$I_C = -500\text{mA}, I_B = -50\text{mA}$	-	-2.6	
<b>SMALL-SIGNAL CHARACTERISTICS</b>					
Current-Gain-Bandwidth Product	$f_T$	$I_C = -50\text{mA}, V_{CE} = -20\text{V}, f = 100\text{MHz}$	200	-	MHz
Delay Time	$t_d$	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$	-	10	$\mu\text{S}$
Rise Time	$t_r$			40	$\mu\text{S}$
Storage Time	$t_s$	$V_{CC} = -6.0\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$	-	80	$\mu\text{S}$
Fall Time	$t_f$			30	$\mu\text{S}$

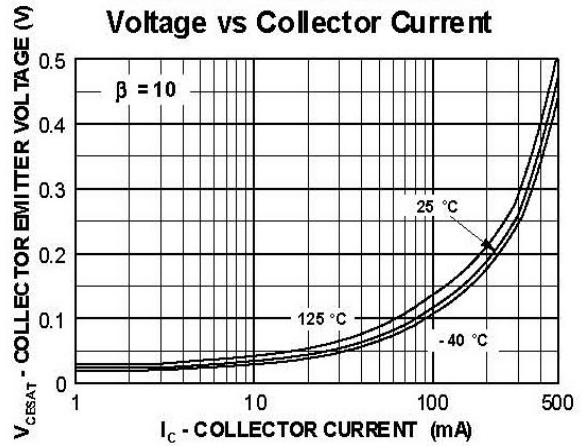
**NOTE:**

1. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ ; Duty Cycle  $\leq 2\%$ .

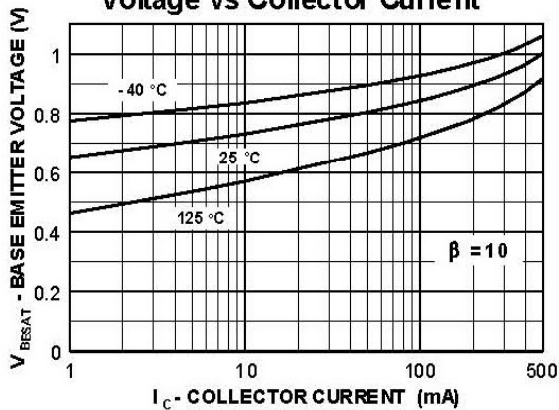
**Typical Pulsed Current Gain vs Collector Current**



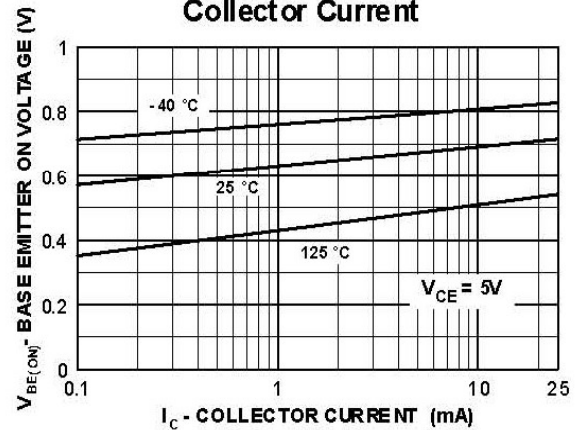
**Collector-Emitter Saturation Voltage vs Collector Current**



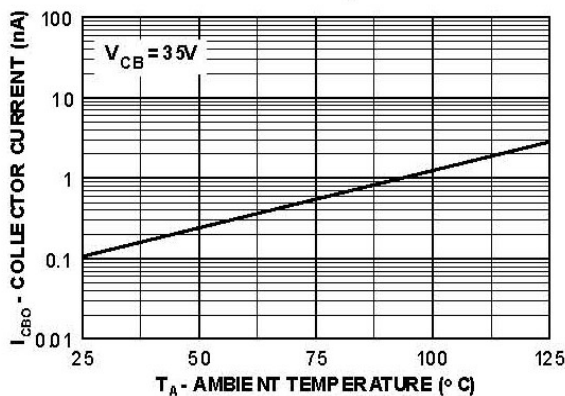
**Base-Emitter Saturation Voltage vs Collector Current**



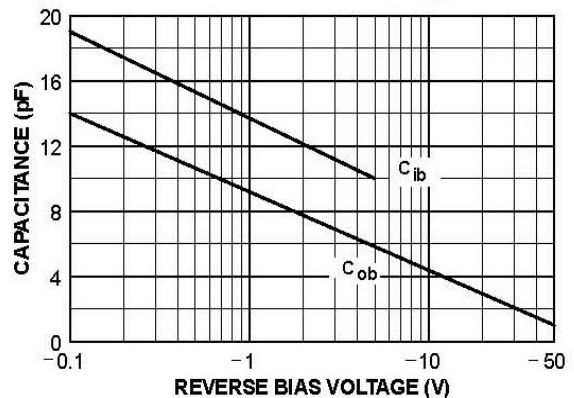
**Base Emitter ON Voltage vs Collector Current**

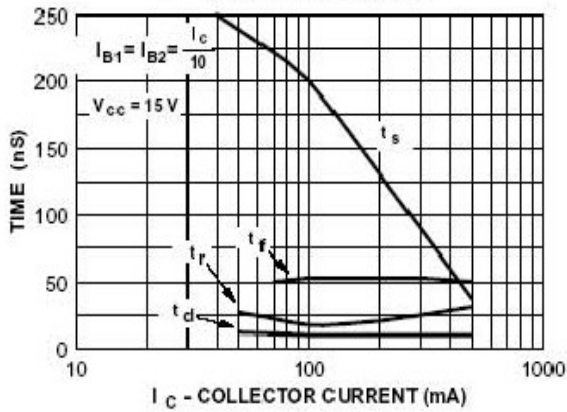
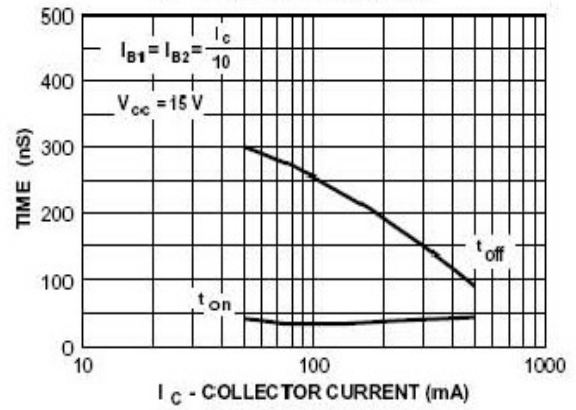
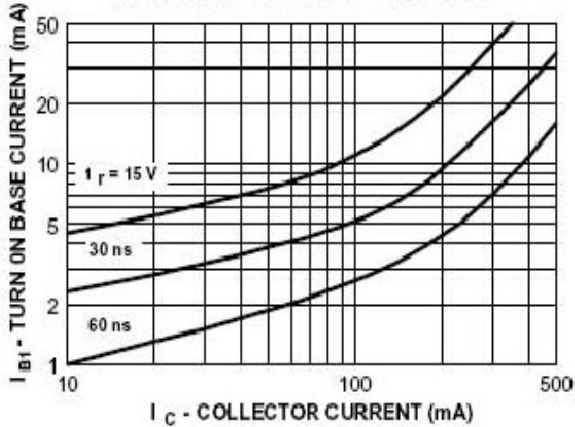
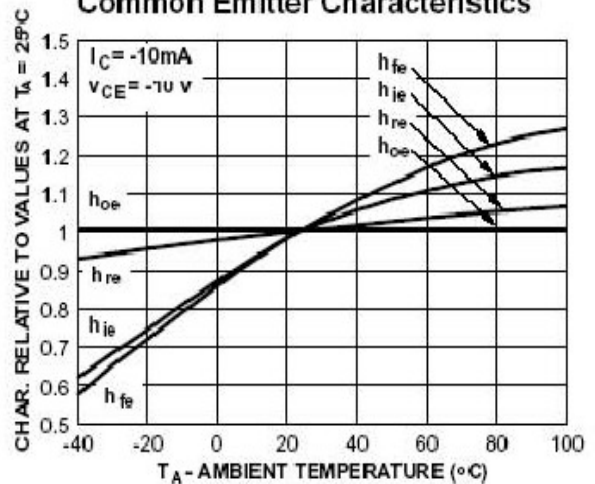
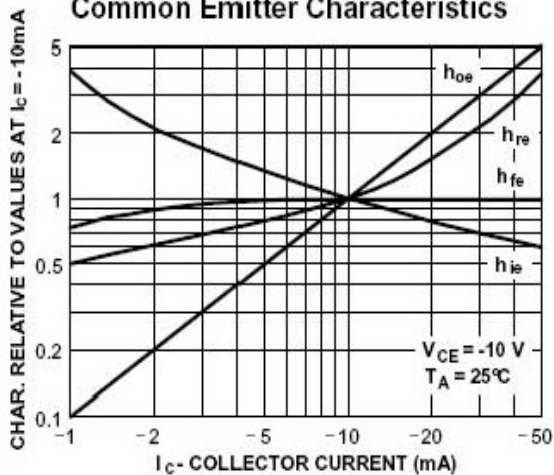
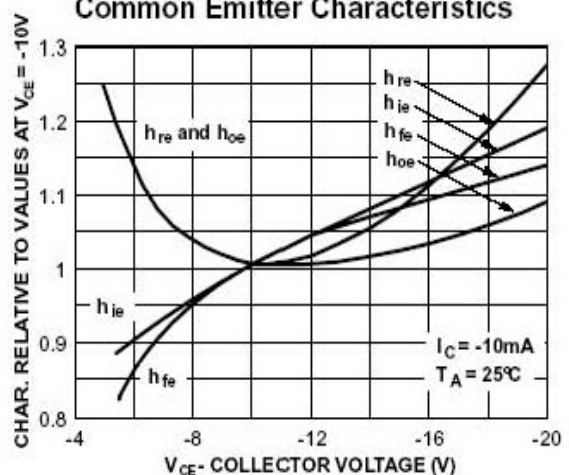


**Collector-Cutoff Current vs Ambient Temperature**

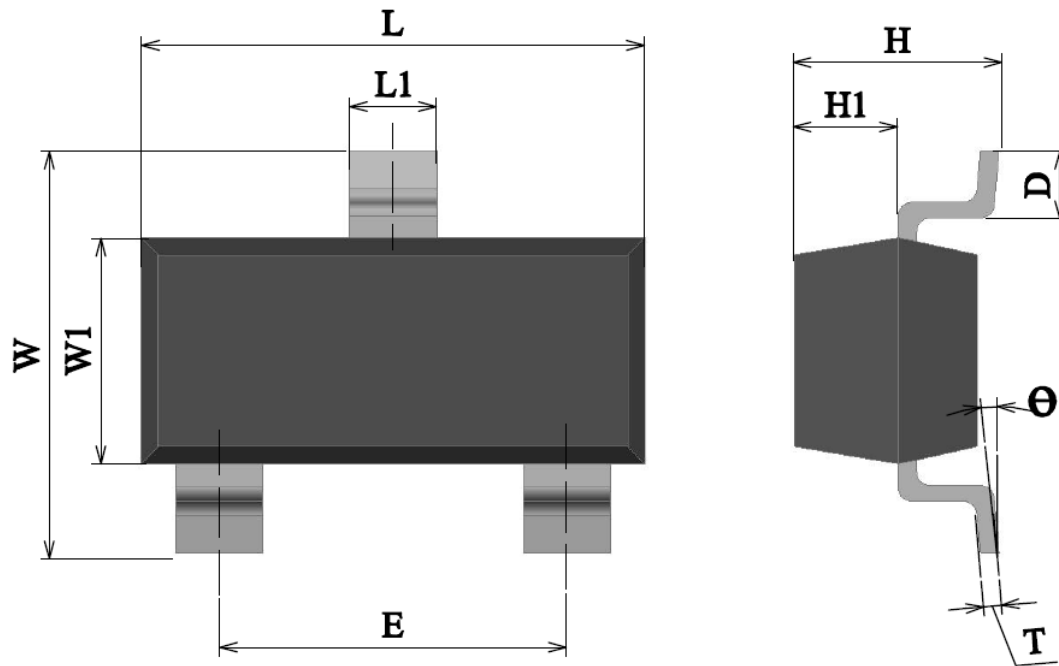


**Input and Output Capacitance vs Reverse Bias Voltage**



**Switching Times vs Collector Current**

**Turn On and Turn Off Times vs Collector Current**

**Rise Time vs Collector and Turn On Base Currents**

**Common Emitter Characteristics**

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## SOT-23 DIMENSION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
L	2.80	3.10	0.110	0.122
L1	0.30	0.50	0.012	0.020
W	2.25	2.54	0.089	0.100
W1	1.20	1.40	0.047	0.055
E	1.80	2.00	0.071	0.079
H	0.90	1.15	0.035	0.045
H1	0.40	0.80	0.016	0.031
D	0.30	0.50	0.012	0.020
T	0.08	0.15	0.003	0.006
θ	0°	8°	0°	8°